

PART NUMBER MM54HC154JS883-ROCV

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Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
 - Class Q Military
 - Class V Space Level

Qualified Suppliers List of Distributors (QSLD)

 Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

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MM54HC154/MM74HC154 4-to-16 Line Decoder

General Description

This decoder utilizes advanced silicon-gate CMOS technology, and is well suited to memory address decoding or data routing applications. It possesses high noise immunity, and low power consumption of CMOS with speeds similar to low power Schottky TTL circuits.

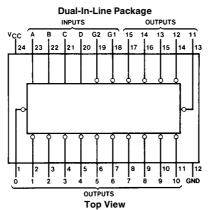
The MM54HC154/MM74HC154 have 4 binary select inputs (A, B, C, and D). If the device is enabled these inputs determine which one of the 16 normally high outputs will go low. Two active low enables ($\overline{\text{G1}}$ and $\overline{\text{G2}}$) are provided to ease cascading of decoders with little or no external logic.

Each output can drive 10 low power Schottky TTL equivalent loads, and is functionally and pin equivalent to the 54LS154/74LS154. All inputs are protected from damage due to static discharge by diodes to V_{CC} and ground.

Features

- Typical propagation delay: 21 ns
- Power supply quiescent current: 80 µA (74HC)
- Wide power supply voltage range: 2-6V
- Low input current: 1 µA maximum

Connection Diagram



TL/F/5122-1

Order Number MM54HC154 or MM74HC154

Truth Table

Inputs						Low
G1	G2	D	С	В	Α	Output*
L	L	L	L	L	L	0
L	L	L	L	L	Н	1
L	L	L	L	Н	L	2
L	L	L	L	Н	Н	3
L	L	L	Н	L	L	4
L	L	L	Н	L	Н	5
L	L	L	Н	Н	L	6
L	L	L	Н	Н	Н	7
L	L	Н	L	L	L	8
L	L	Н	L	L	Н	9
L	L	Н	L	Н	L	10
L	L	Н	L	Н	Н	11
L	L	Н	Н	L	L	12
L	L	Н	Н	L	Н	13
L	L	Н	Н	Н	L	14
L	L	Н	Н	Н	Н	15
L	Н	Х	X	Χ	Χ	_
Н	L	X	Χ	Χ	Χ	_
Н	Н	Х	Χ	Х	Х	_

^{*}All others high

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Absolute Maximum Ratings (Notes 1 & 2) If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

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Supply Voltage (V _{CC})	-0.5 to $+7.0$ V
DC Input Voltage (V _{IN})	-1.5 to $V_{\rm CC}$ $+1.5$ $V_{\rm CC}$
DC Output Voltage (V _{OUT})	-0.5 to $V_{\rm CC}$ $+$ 0.5 $V_{\rm CC}$
Clamp Diode Current (I _{IK} , I _{OK})	\pm 20 mA
DC Output Current, per pin (I _{OUT})	\pm 25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	\pm 50 mA
Storage Temperature Range (T _{STG})	-65°C to $+150$ °C
Dawer Dissipation (D.)	

 Power Dissipation (PD)
 600 mW

 (Note 3)
 500 mW

 S.O. Package only
 500 mW

 Lead Temp. (TL) (Soldering 10 seconds)
 260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V _{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T _A)			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C
Input Rise or Fall Times			
$(t_r, t_f) V_{CC} = 2.0V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	v _{cc}	T _A =25°C		74HC T _A = -40 to 85°C	54HC T _A = -55 to 125°C	Units	
				Тур		Guaranteed Limits			
V _{IH}	Minimum High		2.0V		1.5	1.5	1.5	٧	
	Level Input		4.5V		3.15	3.15	3.15	V	
	Voltage		6.0V		4.2	4.2	4.2	V	
V_{IL}	Maximum Low		2.0V		0.5	0.5	0.5	V	
	Level Input		4.5V		1.35	1.35	1.35	V	
	Voltage**		6.0V		1.8	1.8	1.8	V	
V_{OH}	Minimum High	V _{IN} =V _{IH} or V _{IL}							
	Level Output	I _{OUT} ≤20 μA	2.0V	2.0	1.9	1.9	1.9	V	
	Voltage		4.5V	4.5	4.4	4.4	4.4	V	
			6.0V	6.0	5.9	5.9	5.9	V	
		V _{IN} =V _{IH} or V _{IL}							
		$ I_{OUT} \le 4.0 \text{ mA}$	4.5V	4.2	3.98	3.84	3.7	V	
		I _{OUT} ≤5.2 mA	6.0V	5.7	5.48	5.34	5.2	V	
V_{OL}	Maximum Low	V _{IN} =V _{IH} or V _{IL}							
	Level Output	I _{OUT} ≤20 μA	2.0V	0	0.1	0.1	0.1	V	
	Voltage		4.5V	0	0.1	0.1	0.1	V	
			6.0V	0	0.1	0.1	0.1	V	
		$V_{IN} = V_{IH}$ or V_{IL}							
		$ I_{OUT} \le 4.0 \text{ mA}$	4.5V	0.2	0.26	0.33	0.4	V	
		I _{OUT} ≤5.2 mA	6.0V	0.2	0.26	0.33	0.4	V	
I _{IN}	Maximum Input Current	V _{IN} =V _{CC} or GND	6.0V		±0.1	±1.0	±1.0	μΑ	
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		8.0	80	160	μΑ	

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V \pm 10% the worst case output voltages (V_{OH} , and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} =5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} , and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

^{**} V_{IL} limits are currently tested at 20% of V_{CC} . The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

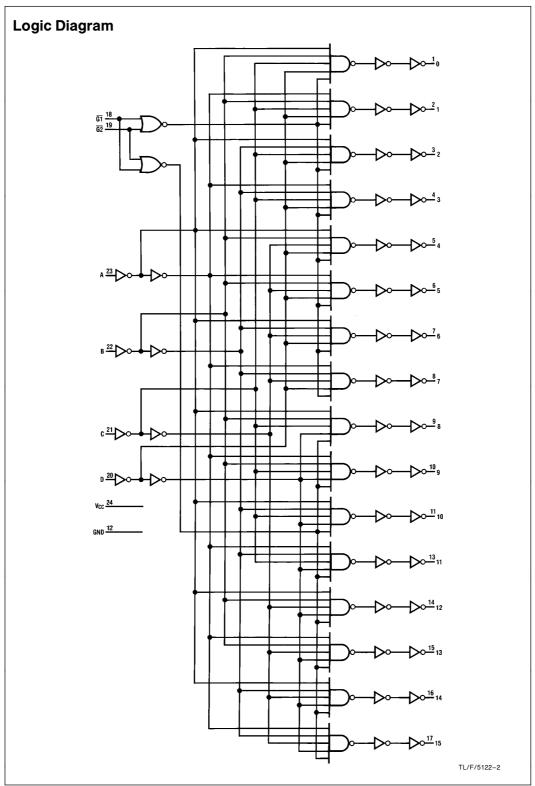
AC Electrical Characteristics $V_{CC}=5V$, $T_A=25^{\circ}C$, $C_L=15$ pF, $t_r=t_f=6$ ns

Symbol	Parameter	Conditions	Тур	Guaranteed Limit	Units
t _{PHL} , t _{PLH}	Maximum Propagation Delay, G1, G2 or A, B, C, D		21	32	ns

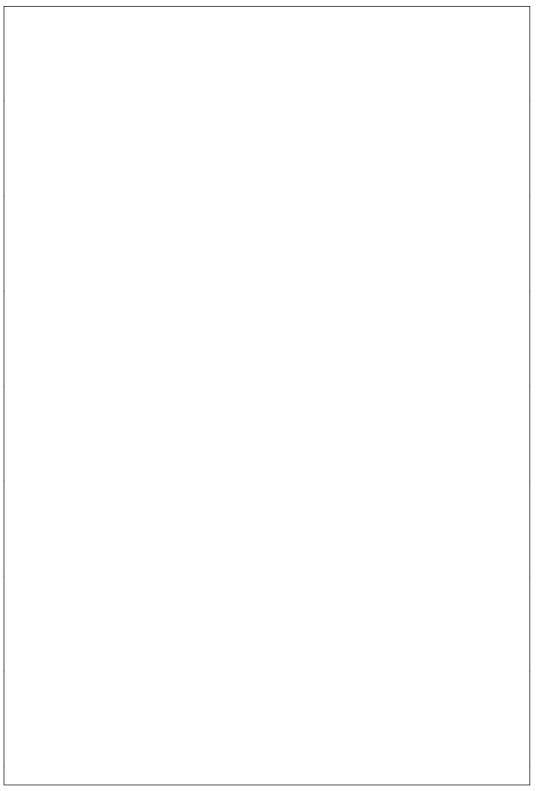
$\textbf{AC Electrical Characteristics} \ \ V_{CC} = 2.0 \ V \ \text{to 6.0 V}, \ C_L = 50 \ \text{pF}, \ t_f = t_f = 6 \ \text{ns (unless otherwise specified)}$

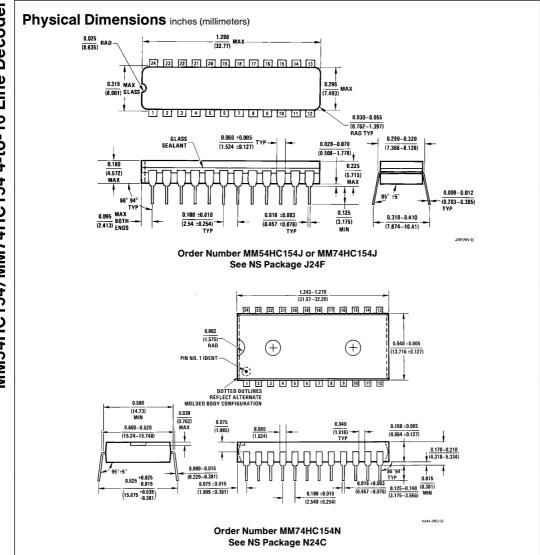
Symbol	Parameter	Conditions	v _{cc}	T _A = 25°C		74HC T _A = -40 to 85°C	54HC T _A = -55 to 125°C	Units	
				Тур	Guaranteed Limits				
t _{PHL} , t _{PLH}	Maximum Propagation Delay, G1 or G2 or A, B, C, D		2.0V 4.5V 6.0V	63 24 20	160 36 30	190 42 35	220 46 39	ns ns ns	
t _{TLH} , t _{THL}	Maximum Output Rise and Fall Time		2.0V 4.5V 6.0V	25 7 6	75 15 13	95 19 16	110 22 19	ns ns ns	
C _{PD}	Power Dissipation Capacitance (Note 5)			90				pF	
C _{IN}	Maximum Input Capacitance			5	10	10	10	pF	

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} \ V_{CC}^2 \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC}$.



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